

Chris Jeynes

List of Publications by Year in descending order

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290
papers

5,124
citations

126858

33
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138417

58
g-index

303
all docs

303
docs citations

303
times ranked

3968
citing authors

#	ARTICLE	IF	CITATIONS
1	Halo Properties in Helium Nuclei from the Perspective of Geometrical Thermodynamics. Annalen Der Physik, 2022, 534, 2100278.	0.9	8
2	Ion beam analysis for cultural heritage. , 2021, , 335-364.		3
3	Differential cross sections for ${}^7\text{Li}({}^3\text{He},p)({}^4\text{He},n){}^9\text{Be}$, ${}^7\text{Li}({}^3\text{He},d)({}^8\text{Be},n){}^9\text{Be}$ and ${}^6\text{Li}({}^3\text{He},p)({}^8\text{Be},n){}^9\text{Be}$ from 1.2 to 3 MeV. Nuclear Instruments & Methods in Physics Research B, 2021, 494-495, 23-28.	0.6	2
4	Entropic uncertainty principle, partition function and holographic principle derived from Liouville's Theorem. Physics Open, 2021, 7, 100068.	0.7	9
5	A Relativistic Entropic Hamiltonian—Lagrangian Approach to the Entropy Production of Spiral Galaxies in Hyperbolic Spacetime. Universe, 2021, 7, 325.	0.9	10
6	External beam Total-IBA using DataFurnace. Nuclear Instruments & Methods in Physics Research B, 2020, 481, 47-61.	0.6	9
7	Fullerene Stability by Geometrical Thermodynamics. ChemistrySelect, 2020, 5, 5-14.	0.7	13
8	On the accuracy of Total-IBA. Nuclear Instruments & Methods in Physics Research B, 2020, 465, 85-100.	0.6	12
9	Quantifying nitrogen in GeSbTe:N alloys. Journal of Analytical Atomic Spectrometry, 2020, 35, 701-712.	1.6	15
10	Maximum Entropy (Most Likely) Double Helical and Double Logarithmic Spiral Trajectories in Space-Time. Scientific Reports, 2019, 9, 10779.	1.6	16
11	Differential elastic backscattering cross-sections of the ${}^2.4\text{ MeV}$ deuterons on sodium. Nuclear Instruments & Methods in Physics Research B, 2019, 461, 124-129.	0.6	1
12	Accurate experimental determination of gallium K- and L ₃ -shell XRF fundamental parameters. Journal of Analytical Atomic Spectrometry, 2018, 33, 1003-1013.	1.6	20
13	RBS as a new primary direct reference method for measuring quantity of material. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 30-31.	0.6	15
14	Nanoscale Properties of Human Telomeres Measured with a Dual Purpose X-ray Fluorescence and Super Resolution Microscopy Gold Nanoparticle Probe. ACS Nano, 2017, 11, 12632-12640.	7.3	17
15	Hypervelocity impact in low earth orbit: finding subtle impactor signatures on the Hubble Space Telescope. Procedia Engineering, 2017, 204, 492-499.	1.2	2
16	Thin film depth profiling by ion beam analysis. Analyst, The, 2016, 141, 5944-5985.	1.7	82
17	Direct quantification of rare earth doped titania nanoparticles in individual human cells. Nanotechnology, 2016, 27, 285103.	1.3	8
18	Fast Assembly of Gold Nanoparticles in Large-Area 2D Nanogrids Using a One-Step, Near-Infrared Radiation-Assisted Evaporation Process. ACS Nano, 2016, 10, 2232-2242.	7.3	41

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19	Costs of open data. Physics World, 2015, 28, 21-21.	0.0	0
20	Electrical properties of Bi-implanted amorphous chalcogenide films. Thin Solid Films, 2015, 589, 369-375.	0.8	6
21	On the traceably accurate voltage calibration of electrostatic accelerators. Nuclear Instruments & Methods in Physics Research B, 2015, 349, 173-183.	0.6	30
22	Accurate electronics calibration for particle backscattering spectrometry. Analytical Methods, 2015, 7, 3096-3104.	1.3	16
23	Certified ion implantation fluence by high accuracy RBS. Analyst, The, 2015, 140, 3251-3261.	1.7	17
24	Physicochemical characteristics and occupational exposure to coarse, fine and ultrafine particles during building refurbishment activities. Journal of Nanoparticle Research, 2015, 17, 1.	0.8	24
25	Development of nanotopography during SIMS characterization of thin films of Ge ¹ Sn alloy. Applied Surface Science, 2015, 356, 422-428.	3.1	1
26	Electrical properties of amorphous chalcogenide/silicon heterojunctions modified by ion implantation. Proceedings of SPIE, 2014, , .	0.8	2
27	Benchmarking experiments for the proton backscattering on ²³ Na, ³¹ P and natS up to 3.5MeV. Nuclear Instruments & Methods in Physics Research B, 2014, 328, 1-7.	0.6	15
28	High accuracy traceable Rutherford backscattering spectrometry of ion implanted samples. Analytical Methods, 2014, 6, 120-129.	1.3	23
29	Effects of dislocation walls on charge carrier transport properties in CdTe single crystal. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 735, 188-192.	0.7	20
30	Particle-Induced X-Ray Emission Analysis. , 2014, , 164-193.		0
31	Double-blind blind. Physics World, 2014, 27, 20-20.	0.0	0
32	Biomass preservation in impact melt ejecta. Nature Geoscience, 2013, 6, 1018-1022.	5.4	28
33	Integrated Ion Beam Analysis (IBA) in Gunshot Residue (GSR) characterisation. Forensic Science International, 2013, 231, 219-228.	1.3	30
34	Measuring and modelling cell-to-cell variation in uptake of gold nanoparticles. Analyst, The, 2013, 138, 7070.	1.7	37
35	A new quantitative method for gunshot residue analysis by ion beam analysis. Analyst, The, 2013, 138, 4649.	1.7	27
36	Fabrication and characterisation of embedded metal nanostructures by ion implantation with nanoporous anodic alumina masks. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 273-276.	0.6	0

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37	High dose ion irradiation effects on immiscible AlN/TiN nano-scaled multilayers. Thin Solid Films, 2013, 544, 562-566.	0.8	7
38	Structural analysis of silicon co-implanted with carbon and high energy proton for the formation of the lasing G-centre. Journal of Applied Physics, 2012, 112, 103110.	1.1	9
39	XTEM characterization of modulated ion implantation through self-organized anodic aluminum oxide (AAO) membranes. Materials Research Society Symposia Proceedings, 2012, 1411, 39.	0.1	0
40	Patterned ion beam implantation of Co ions into a SiO ₂ thin film via ordered nanoporous alumina masks. Nanotechnology, 2012, 23, 045605.	1.3	4
41	Carrier Control in Polycrystalline ZnO:Ga Thin Films via Nitrogen Implantation. ECS Journal of Solid State Science and Technology, 2012, 1, P237-P240.	0.9	1
42	Adsorption and diffusion of strontium in simulated rock fractures quantified via ion beam analysis. Mineralogical Magazine, 2012, 76, 3203-3215.	0.6	2
43	Temperature-dependant study of phosphorus ion implantation in germanium. AIP Conference Proceedings, 2012, , .	0.3	3
44	In situ analysis of cadmium sulphide chemical bath deposition by an optical fibre monitor. Thin Solid Films, 2012, 525, 1-5.	0.8	3
45	Ion irradiation induced Al-Ti interaction in nano-scaled Al/Ti multilayers. Applied Surface Science, 2012, 258, 2043-2046.	3.1	20
46	Accurate Determination of Quantity of Material in Thin Films by Rutherford Backscattering Spectrometry. Analytical Chemistry, 2012, 84, 6061-6069.	3.2	96
47	Characterization of a-FeSi ₂ /c-Si heterojunctions for photovoltaic applications. Semiconductor Science and Technology, 2012, 27, 035016.	1.0	11
48	Solid phase epitaxial re-growth of Sn ion implanted germanium thin films. AIP Conference Proceedings, 2012, , .	0.3	3
49	“Total IBA” Where are we?. Nuclear Instruments & Methods in Physics Research B, 2012, 271, 107-118.	0.6	102
50	Ion Beam Analysis: A Century of Exploiting the Electronic and Nuclear Structure of the Atom for Materials Characterisation. , 2012, , 41-82.		2
51	Ion Beam, SEM and EDXRS Analysis on Doped SiO ₂ Optical Fibres. Progress in Nuclear Science and Technology, 2012, 3, 116-119.	0.3	0
52	1425 poster LASER-PLASMA ACCELERATION OF PARTICLES FOR PROTON AND ION-BEAM RADIOTHERAPY: AN UPDATE FROM THE LIBRA CONSORTIUM. Radiotherapy and Oncology, 2011, 99, S530.	0.3	0
53	Ion Beam Analysis: A Century of Exploiting the Electronic and Nuclear Structure of the Atom for Materials Characterisation. Reviews of Accelerator Science and Technology, 2011, 04, 41-82.	0.5	37
54	Synthesis and Some Properties of Metal Organic Chemical Vapour Deposited Lithium Chromium Oxide Thin Films. Journal of Materials Science Research, 2011, 1, .	0.1	3

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55	High-energy heavy ion beam annealing effect on ion beam synthesis of silicon carbide. Surface and Coatings Technology, 2011, 206, 770-774.	2.2	9
56	Elemental and structural studies at the bone-cartilage interface. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 652, 786-790.	0.7	8
57	Development of a reference database for Ion Beam Analysis and future perspectives. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 2972-2978.	0.6	37
58	Krypton and helium irradiation damage in neodymium-zirconolite. Journal of Nuclear Materials, 2011, 416, 221-224.	1.3	13
59	Krypton irradiation damage in Nd-doped zirconolite and perovskite. Journal of Nuclear Materials, 2011, 415, 67-73.	1.3	16
60	Optimization and Characterisation of Amorphous Iron Disilicide formed by Ion Beam Mixing of Fe-Si Multilayer Structures for Photovoltaic Applications. , 2011, , .		6
61	Measurements and Evaluation of Differential Cross-sections for In Beam Analysis. Journal of the Korean Physical Society, 2011, 59, 2010-2013.	0.3	1
62	Germanium implanted Bragg gratings in silicon on insulator waveguides. Proceedings of SPIE, 2010, , .	0.8	4
63	Synchrotron and ion beam studies of the bone-cartilage interface. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 619, 330-337.	0.7	6
64	On artefacts in the secondary ion mass spectrometry profiling of high fluence H+ implants in GaAs. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2051-2055.	0.6	6
65	Microbeam PIXE analysis of platinum resistant and sensitive ovarian cancer cells. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2168-2171.	0.6	10
66	19th International Conference on Ion Beam Analysis. Nuclear Instruments & Methods in Physics Research B, 2010, 268, v.	0.6	1
67	Ion irradiation stability of multilayered AlN/TiN nanocomposites. Journal Physics D: Applied Physics, 2010, 43, 065302.	1.3	25
68	Synthesis and Some Properties of Metal Organic Chemical Vapour Deposited Molybdenum Oxysulphide Thin Films. Journal of Materials Science and Technology, 2010, 26, 552-557.	5.6	10
69	SU-GG-T-487: Lack of Dose Rate Effect with Ultra-High Dose Rate Irradiation of Normal Tissue Fibroblasts and RT112 Tumour Cells. Medical Physics, 2010, 37, 3299-3299.	1.6	0
70	Characterisation of thin film chalcogenide PV materials using MeV ion beam analysis. , 2009, , .		2
71	Trace element profiling of gunshot residues by PIXE and SEM-EDS: a feasibility study. X-Ray Spectrometry, 2009, 38, 190-194.	0.9	29
72	Accurate determination of the Ca:P ratio in rough hydroxyapatite samples by SEM-EDS, PIXE and RBS-a comparative study. X-Ray Spectrometry, 2009, 38, 343-347.	0.9	37

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73	High concentration Mn ion implantation in Si. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1623-1625.	0.6	16
74	Characterisation of inhomogeneous inclusions in Darwin glass using ion beam analysis. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2219-2224.	0.6	13
75	Characterisation of gunshot residue particles using self-consistent ion beam analysis. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2265-2268.	0.6	13
76	Metal deposition at the bone-cartilage interface in articular cartilage. Applied Radiation and Isotopes, 2009, 67, 475-479.	0.7	15
77	The thermoluminescence response of doped SiO ₂ optical fibres subjected to photon and electron irradiations. Applied Radiation and Isotopes, 2009, 67, 423-427.	0.7	84
78	Ion Beam Modification of Al/Ti Multilayers. Materials and Manufacturing Processes, 2009, 24, 1130-1133.	2.7	5
79	Time, the multiverse and belief. Physics World, 2009, 22, 15-16.	0.0	0
80	Advanced physics and algorithms in the IBA DataFurnace. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1875-1879.	0.6	145
81	Reduction of bacterial adhesion on ion-implanted stainless steel surfaces. Medical Engineering and Physics, 2008, 30, 341-349.	0.8	48
82	Interactions of photoresist stripping plasmas with nanoporous organo-silicate ultra low dielectric constant dielectrics. Thin Solid Films, 2008, 516, 3697-3703.	0.8	7
83	Summary of IAEA intercomparison of IBA software. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1338-1342.	0.6	69
84	Status of the problem of nuclear cross section data for IBA. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1198-1202.	0.6	20
85	Characterization of paint layers by simultaneous self-consistent fitting of RBS/PIXE spectra using simulated annealing. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1871-1874.	0.6	27
86	RBS/EBS/PIXE measurement of single-walled carbon nanotube modification by nitric acid purification treatment. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1569-1573.	0.6	11
87	On the ion irradiation stability of Al/Ti versus AlN/TiN multilayers. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1749-1753.	0.6	13
88	High fluence nitrogen implantation in Al/Ti multilayers. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2503-2506.	0.6	1
89	Accurate ion beam analysis in the presence of surface roughness. Journal Physics D: Applied Physics, 2008, 41, 205303.	1.3	36
90	Evolution of vacancy-related defects upon annealing of ion-implanted germanium. Physical Review B, 2008, 78, .	1.1	22

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91	Characterisation of Ion Beam Irradiated Zirconolite for Pu Disposition. , 2008, , .		1
92	Maskless proton beam writing in gallium arsenide. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 437-441.	0.6	15
93	Towards truly simultaneous PIXE and RBS analysis of layered objects in cultural heritage. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 426-429.	0.6	18
94	Evaluation of non-Rutherford proton elastic scattering cross-section for magnesium. Nuclear Instruments & Methods in Physics Research B, 2007, 265, 447-452.	0.6	20
95	Depth profile analysis for MgB ₂ thin films, formed by B implantation in Mg ribbons using energetic ion backscatterings. Physica C: Superconductivity and Its Applications, 2007, 460-462, 600-601.	0.6	0
96	Preparation and characterization of metalorganic chemical vapor deposited nickel oxide and lithium nickel oxide thin films. Journal of Materials Science, 2007, 42, 2758-2765.	1.7	14
97	Bacterial adhesion on ion-implanted stainless steel surfaces. Applied Surface Science, 2007, 253, 8674-8681.	3.1	27
98	International Atomic Energy Agency intercomparison of ion beam analysis software. Nuclear Instruments & Methods in Physics Research B, 2007, 262, 281-303.	0.6	84
99	Effect of Irradiation-Induced Disorder on the Conductivity and Critical Temperature of the Organic Superconductor (BEDT)TTF ₂ Cu(SCN) ₂ . Physical Review Letters, 2006, 96, 177002.	2.9	86
100	Distribution of Surfactants in Latex Films: A Rutherford Backscattering Study. Langmuir, 2006, 22, 5314-5320.	1.6	24
101	1,1,1,5,5,5-Hexafluoroacetylacetonate Copper(I) Poly(vinylsiloxane)s as Precursors for Copper Direct-write. Chemistry of Materials, 2006, 18, 2489-2498.	3.2	11
102	Modeling and experimental analysis of InGaN MOVPE in the Aixtron AIX 200/4 RF-S horizontal reactor. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1620-1623.	0.8	11
103	Accurate simulation of backscattering spectra in the presence of sharp resonances. Nuclear Instruments & Methods in Physics Research B, 2006, 247, 381-389.	0.6	23
104	High lateral resolution 2D mapping of the B/C ratio in a boron carbide film formed by femtosecond pulsed laser deposition. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 454-457.	0.6	14
105	Characterising ion-cut in GaAs by Rutherford backscattering spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 429-431.	0.6	3
106	Proton beam lithography at the University of Surrey's Ion Beam Centre. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 387-389.	0.6	9
107	Quality assurance in an implantation laboratory by high accuracy RBS. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 482-485.	0.6	6
108	Elemental content of erythrocytes from patients undergoing Coronary Artery Bypass Grafting (CABG) surgery using PIXE analysis. Journal of Radioanalytical and Nuclear Chemistry, 2006, 269, 619-623.	0.7	3

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109	In situ water permeation measurement using an external $^3\text{He}^{2+}$ ion beam. <i>Journal of Membrane Science</i> , 2006, 285, 137-143.	4.1	7
110	A round robin characterisation of the thickness and composition of thin to ultra-thin AlNO films. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 227, 397-419.	0.6	5
111	Characterisation of the University of Surrey Ion Beam Centre in-air scanning microbeam. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 231, 26-31.	0.6	12
112	New developments on the Surrey microbeam applications to lithography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 231, 428-432.	0.6	11
113	Comparison of elemental boron and boron halide implants into silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 237, 93-97.	0.6	3
114	The influence of the ion implantation temperature and the flux on smart-cut [®] in GaAs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 237, 193-196.	0.6	11
115	Electrical activation of solid-phase epitaxially regrown ultra-low energy boron implants in Ge preamorphised silicon and SOI. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 237, 107-112.	0.6	22
116	The influence of the ion implantation temperature and the dose rate on smart-cut [®] in GaAs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 240, 142-145.	0.6	6
117	Preparation and characterization of metallorganic chemical vapour deposited molybdenum (II) oxide (MoO) thin films. <i>Thin Solid Films</i> , 2005, 472, 84-89.	0.8	14
118	Evaluation of BBr ²⁺ and B ⁺⁺ Br ⁺ implants in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 196-199.	1.7	0
119	Preparation and characterization of metallorganic chemical vapour deposited Li _x Mo _y O _z using a single source solid precursor. <i>Ionics</i> , 2005, 11, 387-392.	1.2	4
120	Raman study of the strain and H ₂ preconditioning effect on self-assembled Ge island on Si (001). <i>Journal of Materials Science: Materials in Electronics</i> , 2005, 16, 469-474.	1.1	1
121	The dependence of the radiation damage formation on the substrate implant temperature in GaN during Mg ion implantation. <i>Journal of Applied Physics</i> , 2005, 98, 013515.	1.1	15
122	A Potential Integrated Low Temperature Approach for Superconducting MgB_2 Thin Film Growth and Electronics Device Fabrication by Ion Implantation. <i>IEEE Transactions on Applied Superconductivity</i> , 2005, 15, 3265-3268.	1.1	6
123	Accurate calibration of the retained fluence from a versatile single wafer implanter using RBS. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 217, 177-182.	0.6	1
124	The new Surrey ion beam analysis facility. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 219-220, 405-409.	0.6	78
125	Round Robin: measurement of H implantation distributions in Si by elastic recoil detection. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 222, 547-566.	0.6	23
126	Difference in individual layer properties in cuprate/manganite structures deposited by laser ablation. <i>Annalen Der Physik</i> , 2004, 13, 81-82.	0.9	0

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127	Concentration profiles of antimony-doped shallow layers in silicon. Semiconductor Science and Technology, 2004, 19, 728-732.	1.0	9
128	Influence of interfaces on the rates of crosslinking in poly(dimethyl siloxane) coatings. Journal of Polymer Science Part A, 2004, 42, 1421-1431.	2.5	43
129	Critical review of the current status of thickness measurements for ultrathin SiO ₂ on Si Part V: Results of a CCQM pilot study. Surface and Interface Analysis, 2004, 36, 1269-1303.	0.8	138
130	Bonding structure and hydrogen content in silicon nitride thin films deposited by the electron cyclotron resonance plasma method. Thin Solid Films, 2004, 459, 203-207.	0.8	27
131	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 323-327.	1.1	5
132	Comparison of boron halide, decaborane and B implants in Si from Molecular Dynamics simulations. Nuclear Instruments & Methods in Physics Research B, 2003, 202, 143-148.	0.6	3
133	Distribution of Surfactants near Acrylic Latex Film Surfaces: A Comparison of Conventional and Reactive Surfactants (Surfmers). Langmuir, 2003, 19, 3212-3221.	1.6	89
134	Elemental thin film depth profiles by ion beam analysis using simulated annealing - a new tool. Journal Physics D: Applied Physics, 2003, 36, R97-R126.	1.3	168
135	High quality YBa ₂ /Cu ₃ O _{7-δ} Josephson junctions and junction arrays fabricated by masked proton beam irradiation damage. IEEE Transactions on Applied Superconductivity, 2003, 13, 889-892.	1.1	4
136	Ion beam synthesis of superconducting MgB ₂ thin films. Applied Physics Letters, 2003, 82, 236-238.	1.5	28
137	Josephson effects in MgB ₂ /metal masked ion damage junctions. IEEE Transactions on Applied Superconductivity, 2003, 13, 1071-1074.	1.1	3
138	Realization and properties of YBa ₂ Cu ₃ O _{7-δ} Josephson junctions by metal masked ion damage technique. Applied Physics Letters, 2002, 80, 814-816.	1.5	29
139	Realization and properties of MgB ₂ metal-masked ion damage junctions. Applied Physics Letters, 2002, 81, 3600-3602.	1.5	16
140	Elemental analysis of residual deposits in an ion implanter using IBA techniques. , 2002, , .		0
141	Evaluation of the boron activation and depth distribution using BBr ₂ ⁺ implants. , 2002, , .		2
142	Electrical isolation of n-type InP using MeV iron implantation at different doses and substrate temperatures. Electronics Letters, 2002, 38, 1225.	0.5	5
143	Effects of carbon content and annealing conditions, on the electrical activation of indium implanted silicon. , 2002, , .		0
144	Absolute dose performance of the SWIFT single wafer ion implanter. , 2002, , .		0

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145	Origins and Effects of a Surfactant Excess near the Surface of Waterborne Acrylic Pressure-Sensitive Adhesives. Langmuir, 2002, 18, 4478-4487.	1.6	83
146	Patterned low temperature copper-rich deposits using inkjet printing. Applied Physics Letters, 2002, 81, 5249-5251.	1.5	76
147	A microbeam RBS analysis of low temperature direct-write inkjet deposited copper. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 141-145.	0.6	7
148	Synthesis of amorphous FeSi ₂ by ion beam mixing. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 166-169.	0.6	26
149	Irradiation damage technology for manufacturable Josephson junctions. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 183-188.	0.6	7
150	Monte Carlo simulations of energetic proton beam irradiation damage defect productions in YBCO thin films with Au masks. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 189-195.	0.6	3
151	Applying elastic backscattering spectrometry when the nuclear excitation function has a fine structure. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 237-240.	0.6	21
152	Accurate determination of the stopping power of in Si using Bayesian inference. Nuclear Instruments & Methods in Physics Research B, 2002, 194, 15-25.	0.6	35
153	Optimisation of masked ion irradiation damage profiles in YBCO thin films by Monte Carlo simulation. Physica C: Superconductivity and Its Applications, 2002, 372-376, 55-58.	0.6	1
154	Preparation and characterization of undoped zinc oxide and uranium doped zinc oxide thin films. Optical Materials, 2002, 20, 119-123.	1.7	5
155	Accurate RBS measurement of ion implant doses in silicon. Surface and Interface Analysis, 2002, 33, 478-486.	0.8	29
156	Preparation and characterization of pyrolytically deposited (Co ϵ “Vâ€“O and Cr ϵ “Vâ€“O) thin films. Thin Solid Films, 2002, 402, 49-54.	0.8	9
157	Masked ion damage and implantation for device fabrication. Vacuum, 2002, 69, 11-15.	1.6	9
158	Electrical behaviour of arsenic implanted silicon wafers at large tilt angle. , 2002, , .		1
159	Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. Journal of Applied Physics, 2001, 89, 6044-6047.	1.1	28
160	Amorphous-iron disilicide: A promising semiconductor. Applied Physics Letters, 2001, 79, 1438-1440.	1.5	50
161	...and against.... Physics World, 2001, 14, 19-19.	0.0	2
162	Error performance analysis of artificial neural networks applied to Rutherford backscattering. Surface and Interface Analysis, 2001, 31, 35-38.	0.8	9

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163	Title is missing!. Journal of Materials Science, 2001, 36, 4731-4738.	1.7	6
164	Monte Carlo simulations of masked ion beam irradiation damage profiles in YBa ₂ Cu ₃ O _{7-δ} thin films. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 242-246.	0.6	9
165	Properties of δ -FeSi ₂ grown by combined ion irradiation and annealing of Fe/Si bilayers. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 309-313.	0.6	4
166	An electrostatic beam rocking system on the Surrey nuclear microprobe. Nuclear Instruments & Methods in Physics Research B, 2001, 181, 54-59.	0.6	2
167	Nanometer scale masked ion damage barriers in YBa ₂ /Cu ₃ /O _{7-δ} . IEEE Transactions on Applied Superconductivity, 2001, 11, 780-783.	1.1	6
168	Performance of high-T _c /dc SQUID magnetometers with resistively shunted inductances compared to "unshunted" devices. IEEE Transactions on Applied Superconductivity, 2001, 11, 916-919.	1.1	5
169	Determination of Stopping Power of Ions in Matter. , 2001, , 1105-1110.		0
170	The Effects of Implanted Arsenic on Ti-Silicide Formation. Solid State Phenomena, 2000, 71, 147-172.	0.3	2
171	Accurate depth profiling of complex optical coatings. Surface and Interface Analysis, 2000, 30, 237-242.	0.8	24
172	Vacancy-related defects in ion implanted and electron irradiated silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 143-147.	1.7	7
173	Electrical and optical properties of Co ⁺ ion implanted a-Si _{1-x} C _x :H alloys. Nuclear Instruments & Methods in Physics Research B, 2000, 160, 505-509.	0.6	3
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